

WHAT IS CLAIMED IS:

1. A method of forming an individually patterned layer in a plurality of regions of a substrate, comprising the steps

5 of:

disposing between said substrate and a layer material source a mask including an opening corresponding to one or more of the plurality of regions where said layer is formed; and

causing relative movement between said mask and said layer material source, and said substrate, and causing a material scattered from said layer material source to attach to said substrate through said opening, thereby forming said individually patterned layer.

10 15 2. A method according to claim 1, wherein

said layer material source is a linearly extending source elongated in a direction perpendicular to a direction of the relative movement between said mask and said layer material source, and said substrate.

20 25 3. A method according to claim 2, wherein
said linearly extending source is formed by a plurality of layer material sources arranged adjacent to each other.

4. A method according to claim 1, wherein
said layer is an electroluminescent layer formed between first and second electrodes, and
said layer material is an electroluminescent material.

5. A method according to claim 4, wherein
said electroluminescent material is an organic material
scattered from said layer material source by evaporation and
5 attached to said substrate, thereby forming said
electroluminescent layer.

6. A method according to claim 1, wherein
a semiconductor material is used for said mask.

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7. A method of forming an individually patterned layer
in a plurality of regions of a substrate, comprising the steps
of:

15 disposing between said substrate and a layer material
source a mask having a smaller area than said substrate and
including an opening corresponding to one or more of the
plurality of regions where said layer is formed; and

20 causing relative movement between said mask and said
layer material source, and said substrate, and causing a
material scattered from said layer material source to attach
to said substrate through said opening, thereby forming said
individually patterned layer.

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8. A method according to claim 7, wherein
said layer material source is a linearly extending source
elongated in a direction perpendicular to a direction of the
relative movement between said mask and said layer material
source, and said substrate.

9. A method according to claim 8, wherein
said linearly extending source is formed by a plurality
of layer material sources arranged adjacent to each other.

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10. A method according to claim 7, wherein
a semiconductor material is used for said mask.

11. A manufacturing method of a color emissive device
10 including, on a substrate, a self-emissive element having a
first electrode, an emissive material layer for each color, and
a second electrode, for each of a plurality of pixels, said
method comprising the steps of:

15 disposing between said substrate and an emissive material
source a mask including an opening at a position corresponding
to a region for forming the emissive material layer of one or
more of said plurality of pixels of said substrate; and

20 sliding a relative position between said mask and said
emissive material source, and said substrate by a predetermined
pitch corresponding to a size of the pixel of said substrate,
and causing an emissive material to attach to a predetermined
region of said substrate through said mask, thereby forming the
emissive material layer.

25 12. A manufacturing method of a color emissive device
according to claim 11, wherein

26 said substrate is slid in two directions of said substrate
perpendicular to each other by a pitch corresponding to an

arrangement of said pixels for a same color.

13. A manufacturing method of a color emissive device according to claim 11, wherein

5 said substrate is slid in one direction of said substrate by a pitch corresponding to an arrangement of said pixels for a same color.

14. A manufacturing method of a color emissive device according to claim 11, wherein

10 said emissive material source is a linearly extending source elongated in a direction perpendicular to a direction of the relative movement between said mask and said emissive material source, and said substrate.

15 15. A manufacturing method of a color emissive device according to claim 14, wherein

 said linearly extending source is formed by a plurality of emissive material sources arranged adjacent to each other.

20 16. A manufacturing method of a color emissive device according to claim 11, wherein

 said self-emissive element is an electroluminescent element.

25 17. A manufacturing method of a color emissive device according to claim 11, wherein

 said emissive device is a display device for displaying

an image with a plurality of pixels.

18. A manufacturing method of a color emissive device according to claim 11, wherein

5 a semiconductor material is used for said mask.

19. A manufacturing method of a color emissive device including, on a substrate, a self-emissive element having a first electrode, an emissive material layer for each color, and
10 a second electrode, for each of a plurality of pixels, said method comprising the steps of:

disposing between said substrate and an emissive material source a mask including an opening at a position corresponding to a region for forming the emissive material layer of one or
15 more of said plurality of pixels of said substrate, and having a smaller area than said substrate to cover one or more of said plurality of pixels on said substrate; and

sliding a relative position between said mask and said emissive material source, and said substrate by a predetermined
20 pitch corresponding to a size of the pixel of said substrate, and causing an emissive material to attach to a predetermined region of said substrate through said mask, thereby forming the emissive material layer.

25 20. A manufacturing method of a color emissive device according to claim 19, wherein

said substrate is slid in two directions of said substrate perpendicular to each other by a pitch corresponding to an

arrangement of said pixels for a same color.

21. A manufacturing method of a color emissive device according to claim 19, wherein

5 said substrate is slid in one direction of said substrate by a pitch corresponding to an arrangement of said pixels for a same color.

22. A manufacturing method of a color emissive device
10 according to claim 19, wherein

 said emissive material source is a linearly extending source elongated in a direction perpendicular to a direction of the relative movement between said mask and said emissive material source, and said substrate.

15 23. A manufacturing method of a color emissive device according to claim 22, wherein

 said linearly extending source is formed by a plurality of emissive material sources arranged adjacent to each other.

20 24. A manufacturing method of a color emissive device according to claim 19, wherein

 a semiconductor material is used for said mask.

25 25. A manufacturing method of a display device including, on a substrate, a self-emissive element having a first electrode, an emissive material layer for each color, and a second electrode, for each of a plurality of pixels, said method

comprising the steps of:

disposing between said substrate and an emissive material source a mask including an individual opening for each pixel corresponding to a region for forming the emissive material 5 layer individually patterned for each of said plurality of pixels; and

sliding a relative position between said emissive material source and said substrate and causing an emissive material to attach to a predetermined region of said substrate 10 through the opening of said mask, thereby forming the emissive material layer.

26. A manufacturing method of a display device according to claim 25, wherein

15 said emissive material source is a linearly extending source elongated in one direction.

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